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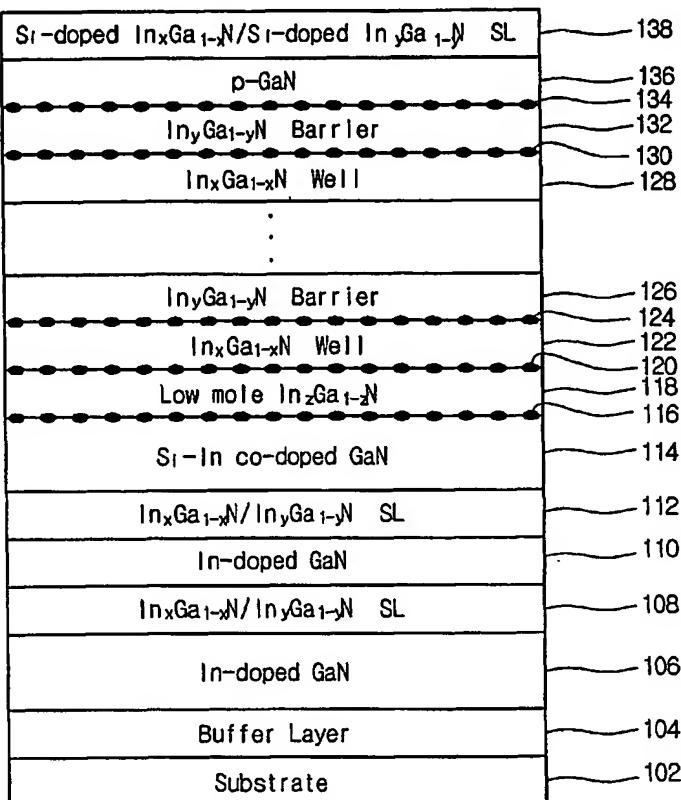
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[Continued on next page]

(54) Title: NITRIDE SEMICONDUCTOR LIGHT EMITTING DEVICE



(57) Abstract: A nitride semiconductor light emitting device is provided. The nitride semiconductor light emitting device includes: an n-type nitride semiconductor layer; an In-containing super lattice structure layer formed above the n-type nitride semiconductor layer; a first electrode contact layer formed above the super lattice structure layer; a first cluster layer formed above the first electrode contact layer; a first In-containing nitride gallium layer formed above the first cluster layer ; a second cluster layer formed above the first In-containing nitride gallium layer ; an active layer formed above the second cluster layer , for emitting light; a p-type nitride semiconductor layer formed above the active layer; and a second electrode contact layer formed above the p-type nitride semiconductor layer.



SK, TR), OAPI (BE, BJ, CE, CG, CI, CM, GA, GN, GQ,  
GW, ML, MR, NE, SN, TD, TG).

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